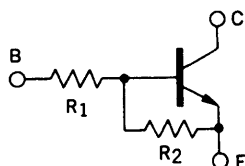


DESCRIPTION The BA1A4P is designed for use in medium speed switching circuit.

FEATURE • Bias resistors built-in type NPN transistor equivalent circuit.



$R_1 = 10 \text{ k}\Omega$

$R_2 = 47 \text{ k}\Omega$

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures

Storage Temperature -55 to $+150$ $^{\circ}\text{C}$

Junction Temperature 150 $^{\circ}\text{C}$ Maximum

Maximum Power Dissipation ($T_a = 25$ $^{\circ}\text{C}$)

Total Power Dissipation 250 mW

Maximum Voltages and Currents ($T_a = 25$ $^{\circ}\text{C}$)

V_{CBO} Collector to Base Voltage 60 V

V_{CEO} Collector to Emitter Voltage 50 V

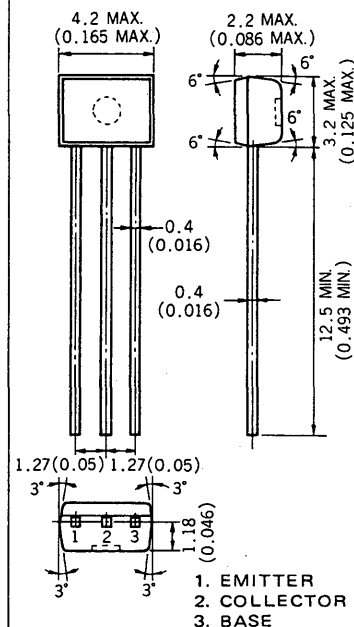
V_{EBO} Emitter to Base Voltage 5.0 V

$I_{C(DC)}$ Collector Current (DC) 100 mA

$I_{C(pulse)}$ Collector Current (pulse) 200 mA

PACKAGE DIMENSIONS

in millimeters (inches)



ELECTRICAL CHARACTERISTICS ($T_a = 25$ $^{\circ}\text{C}$)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
R_1	Input Resistance	7.0	10.0	13.0	$\text{k}\Omega$	
R_2	Input Resistance	32.9	47.0	61.1	$\text{k}\Omega$	
V_{IL}	Low Level Input Voltage		0.65	0.5	V	$V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A}$
V_{IH}	Hi Level Input Voltage	3.0	0.89		V	$V_{CE} = 0.2 \text{ V}, I_C = 5.0 \text{ mA}$
t_{on}	Turn On Time		0.1	0.2	μs	$V_{CC} = 5.0 \text{ V}, R_L = 1.0 \text{ k}\Omega,$ $V_{in} = 5.0 \text{ V},$ $PW = 2 \mu\text{s}, \text{Duty Cycle} \leq 2 \%$
t_{stg}	Storage Time		3.0	5.0	μs	
t_{off}	Turn Off Time		3.2	6.0	μs	
h_{FE1}	DC Current Gain	85	210	340	—	$V_{CE} = 5.0 \text{ V}, I_C = 5.0 \text{ mA}$
h_{FE2}	DC Current Gain	95	370		—	$V_{CE} = 5.0 \text{ V}, I_C = 50 \text{ mA}$
$V_{CE(sat)}$	Collector Saturation Voltage		0.04	0.2	V	$I_C = 5.0 \text{ mA}, I_B = 0.25 \text{ mA}$
I_{CBO}	Collector Cutoff Current			0.1	μA	$V_{CB} = 50 \text{ V}, I_E = 0$

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)